



20N60K-MT

Power MOSFET

20A, 600V N-CHANNEL POWER MOSFET

DESCRIPTION

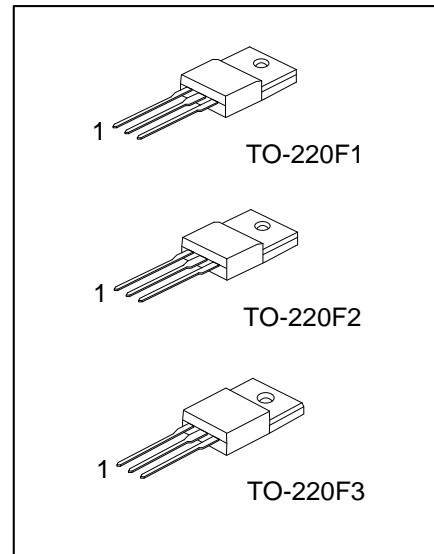
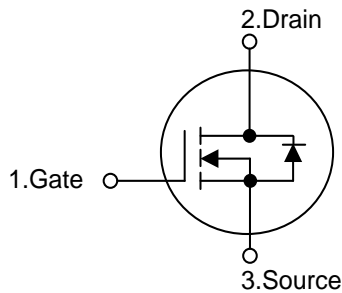
The UTC **20N60K-MT** is an N-channel Power MOSFET using UTC's advanced technology to provide customers a minimum on-state resistance and superior switching performance, etc.

The UTC **20N60K-MT** is generally applied in high efficient AC to DC converters, PWM motor controls and bridge circuits, etc.

FEATURES

- * $R_{DS(ON)} \leq 0.54 \Omega @ V_{GS}=10V, I_D=10A$
- * High Switching Speed
- * Improved dv/dt capability

SYMBOL



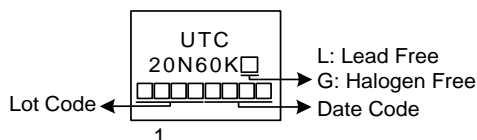
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
20N60KL-TF1-T	20N60KG-TF1-T	TO-220F1	G	D	S	Tube
20N60KL-TF2-T	20N60KG-TF2-T	TO-220F2	G	D	S	Tube
20N60KL-TF3T-T	20N60KG-TF3T-T	TO-220F3	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>20N60KG-TF1-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	600	V
Gate-Source Voltage		V _{GSS}	± 30	V
Drain Current	Continuous	I _D	20	A
	Pulsed (Note 2)	I _{DM}	40	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	731	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.9	V/ns
Power Dissipation		P _D	44	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 10mH, I_{AS} = 12.1A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C

4. I_{SD} ≤ 20A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ _{JA}	62.5	°C/W
Junction to Case	θ _{JC}	2.84	°C/W

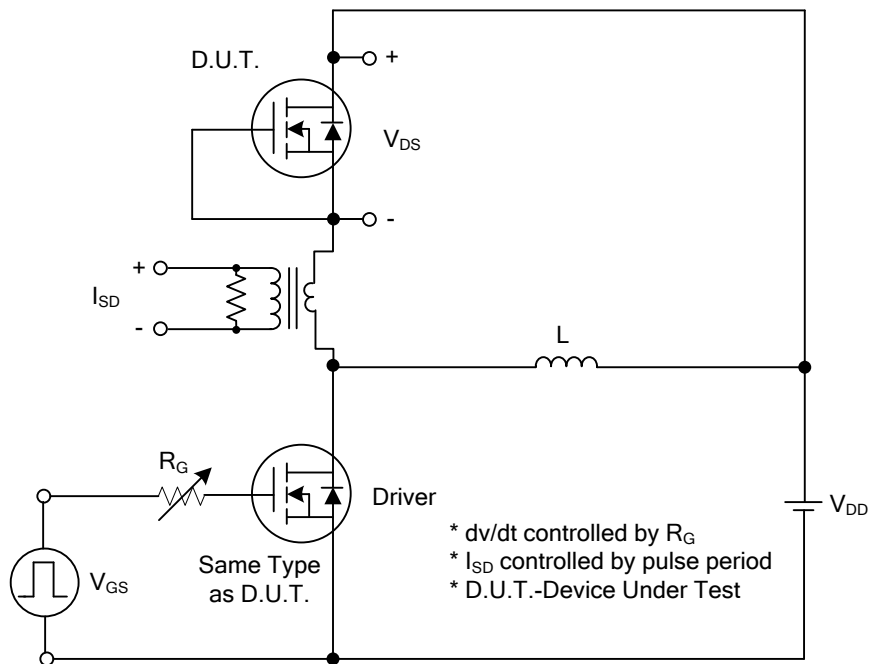
■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D = 250μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A		0.44	0.54	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		2450		pF
Output Capacitance	C _{OSS}			246		pF
Reverse Transfer Capacitance	C _{RSS}			13		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =100V, V _{GS} =10V, I _D =20A I _G =1mA (Note 1, 2)		45		nC
Gate-source Charge	Q _{GS}			11		nC
Gate-drain Charge	Q _{GD}			11		nC
Turn-on Delay Time (Note 1)	t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =20A, R _G =25Ω (Note 1, 2)		26		ns
Rise Time	t _R			24		ns
Turn-off Delay Time	t _{D(OFF)}			158		ns
Fall-Time	t _F			54		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				20	A
Maximum Body-Diode Pulsed Current	I _{SM}				40	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	V _{GS} =0V, I _S =20A			1.4	V
Reverse Recovery Time (Note 1)	t _{rr}	V _{GS} =0V, I _S =20A,		484		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt=100A/μs (Note1)		8.5		μC

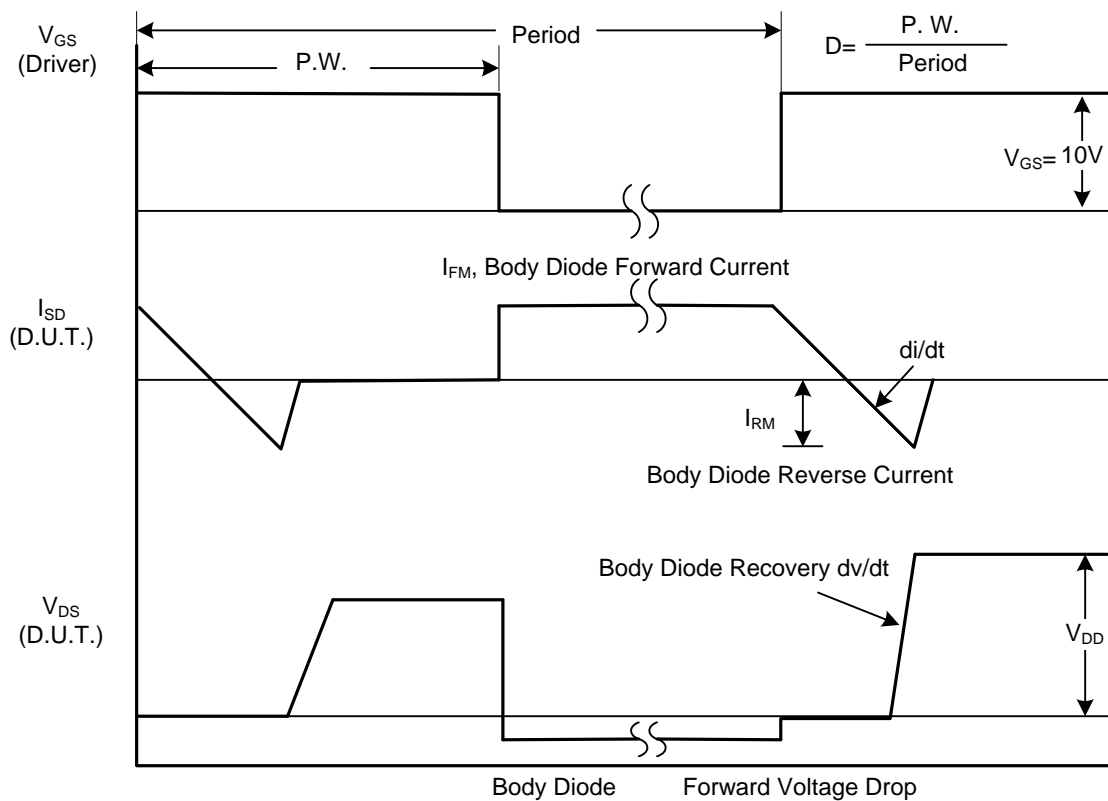
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

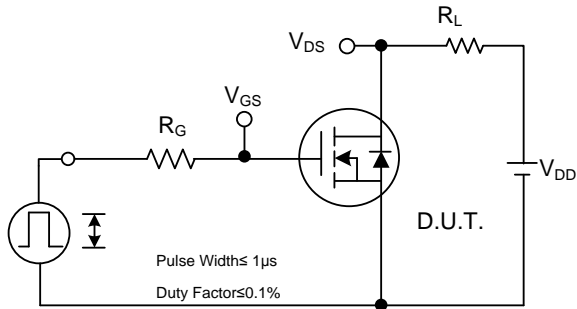


Peak Diode Recovery dv/dt Test Circuit

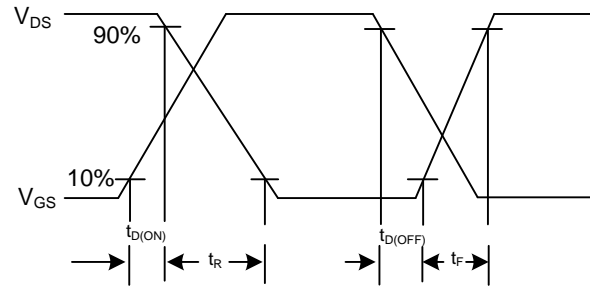


Peak Diode Recovery dv/dt Waveforms

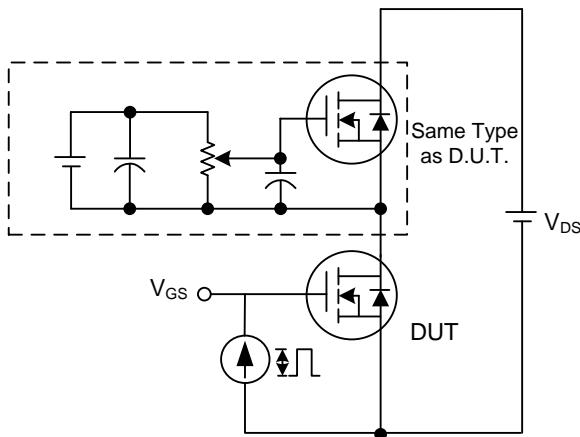
TEST CIRCUITS AND WAVEFORMS



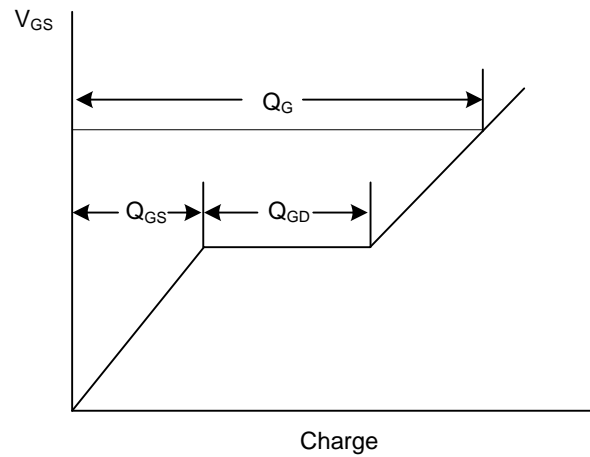
Switching Test Circuit



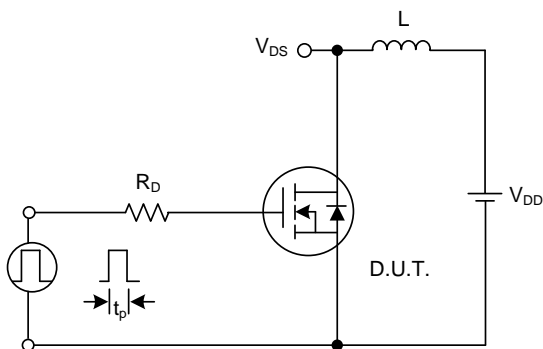
Switching Waveforms



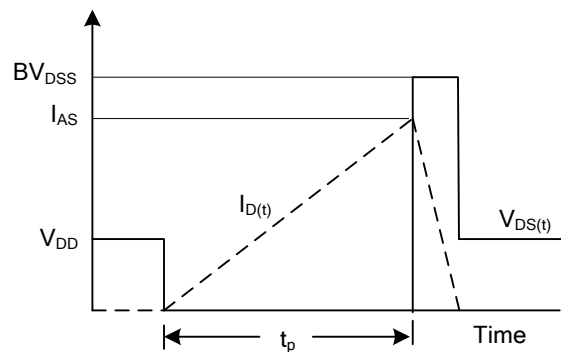
Gate Charge Test Circuit



Gate Charge Waveform

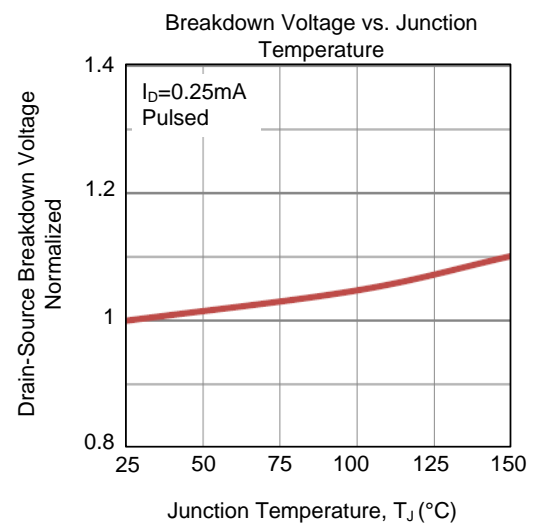
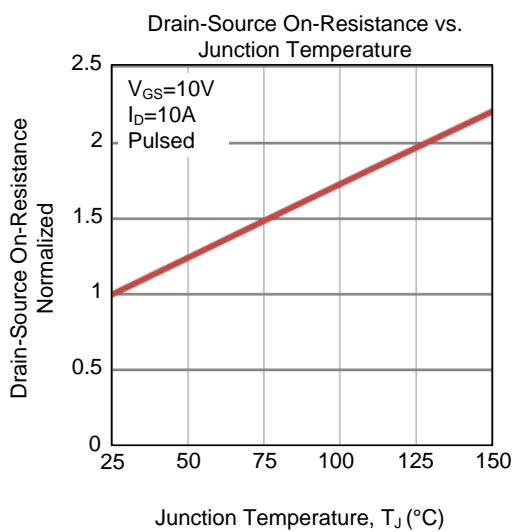
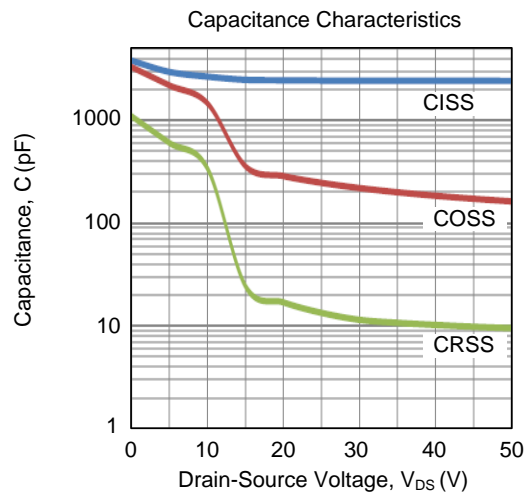
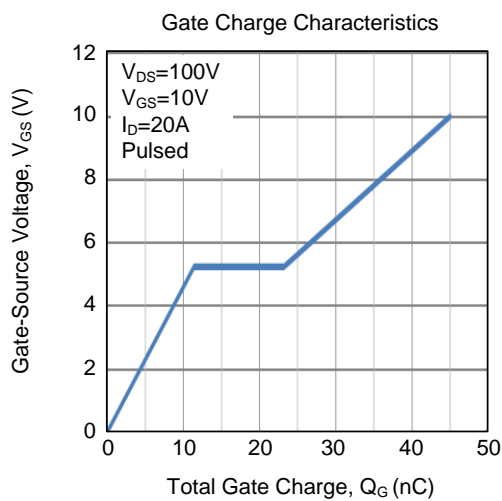
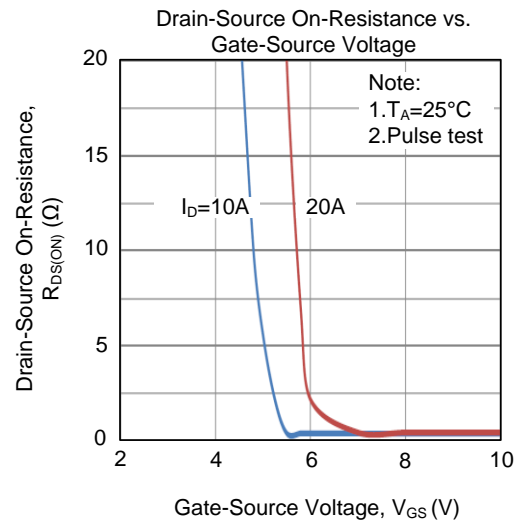
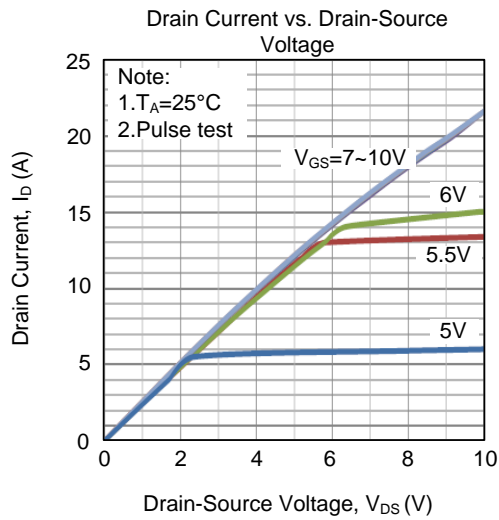


Unclamped Inductive Switching Test Circuit

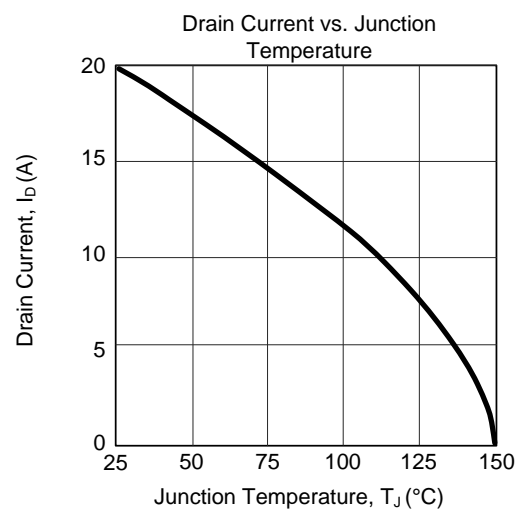
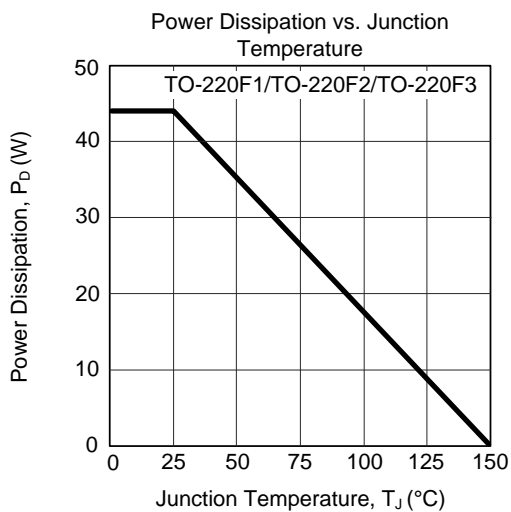
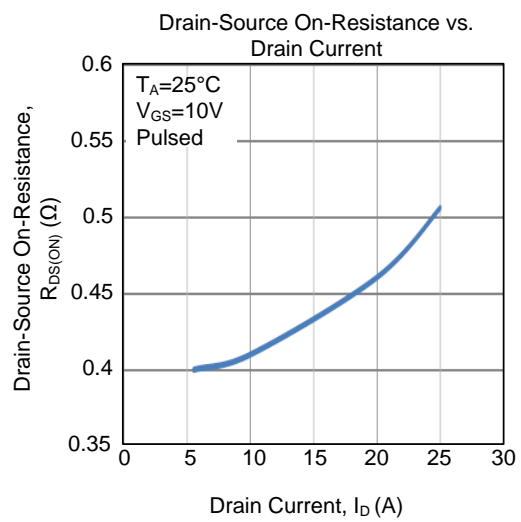
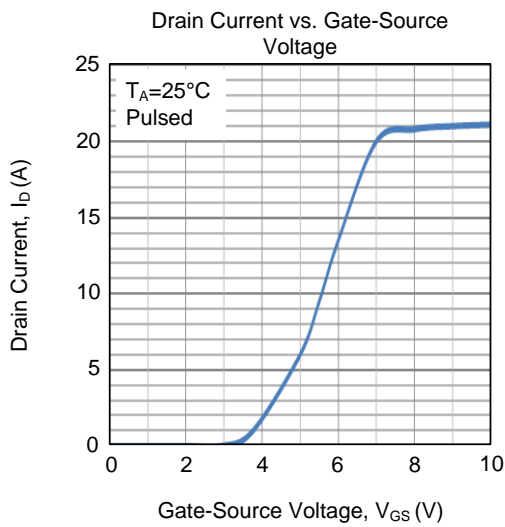
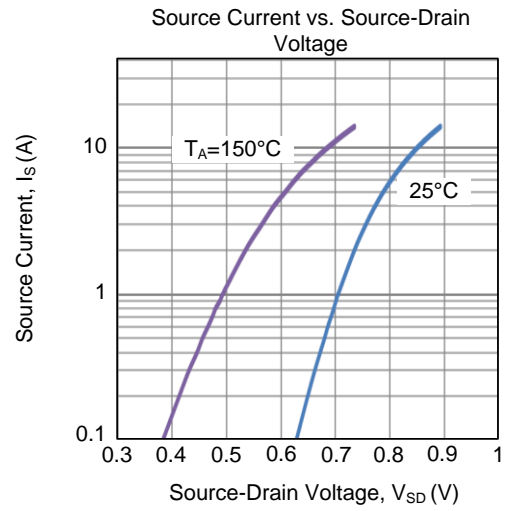
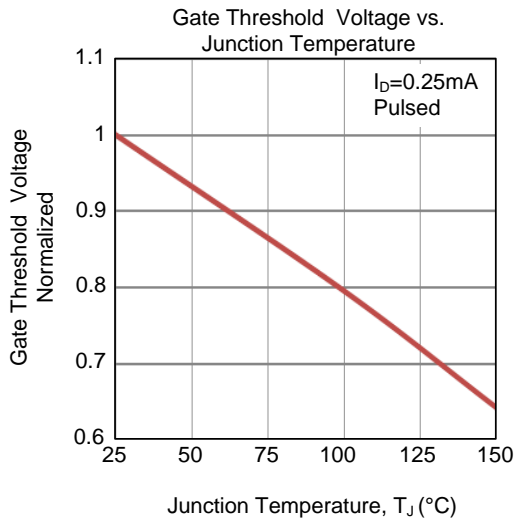


Unclamped Inductive Switching Waveforms

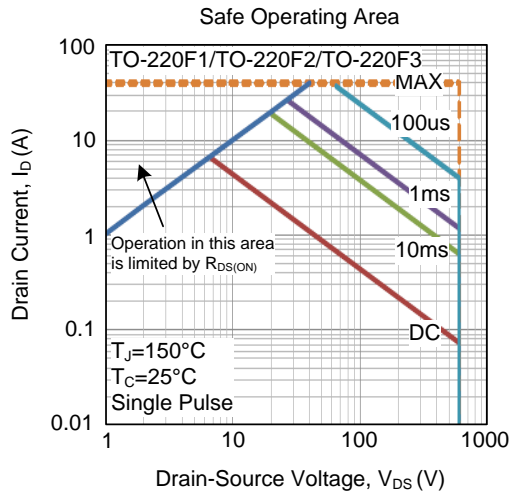
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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